



## DUAL BILATERAL SWITCH

PRELIMINARY DATA

- HIGH SPEED:
  - $t_{PD} = 0.3 \text{ ns}$  (TYP.) at  $V_{CC} = 5V$
  - $t_{PD} = 0.4 \text{ ns}$  (TYP.) at  $V_{CC} = 3.3V$
- LOW POWER DISSIPATION:
  - $I_{CC} = 1 \mu A$  (MAX.) at  $T_A = 25^\circ C$
- LOW "ON" RESISTANCE:
  - $R_{ON} = 10\Omega$  (TYP.) AT  $V_{CC} = 5.0V I_{I/O} = 100\mu A$
  - $R_{ON} = 12\Omega$  (TYP.) AT  $V_{CC} = 3.3V I_{I/O} = 100\mu A$
- SINE WAVE DISTORTION
  - 0.04% (TYP.) AT  $V_{CC} = 3.3V f = 1KHz$
- WIDE OPERATING VOLTAGE RANGE:
  - $V_{CC}$  (OPR) = 2V to 5V

### DESCRIPTION

The 74V2G66 is an high-speed CMOS DUAL BILATERAL SWITCH fabricated in silicon gate C2MOS technology. It achieves high speed propagation delay and VERY LOW ON resistances while maintaining true CMOS low power consumption. This feature makes this part ideal for battery-powered equipment. This bilateral switch handles rail to rail analog and digital signals that may vary across the full

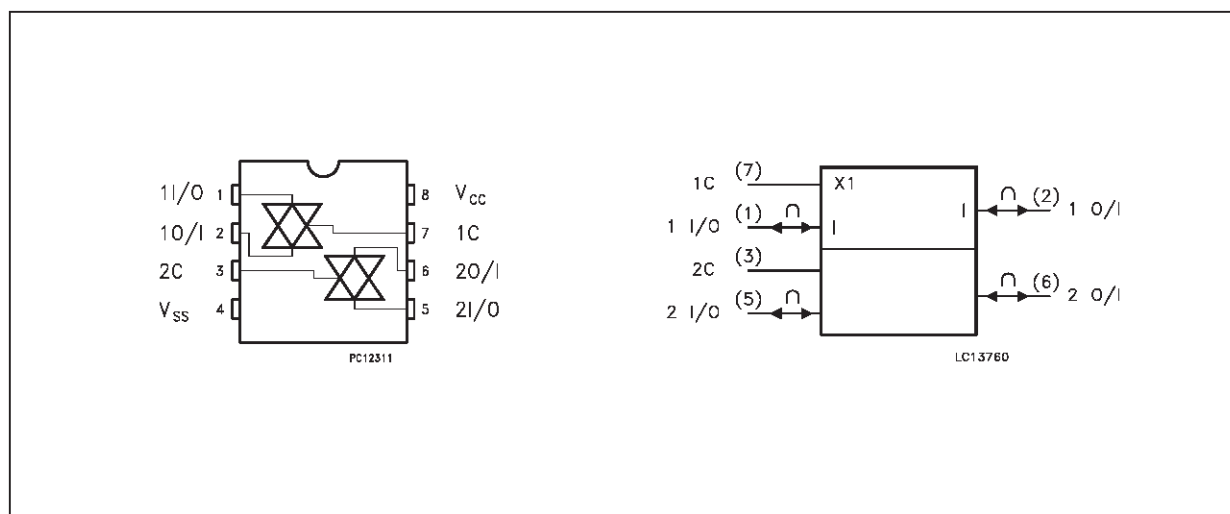


ORDER CODES		
PACKAGE	TUBE	T & R
SOT23-8L		74V2G66STR

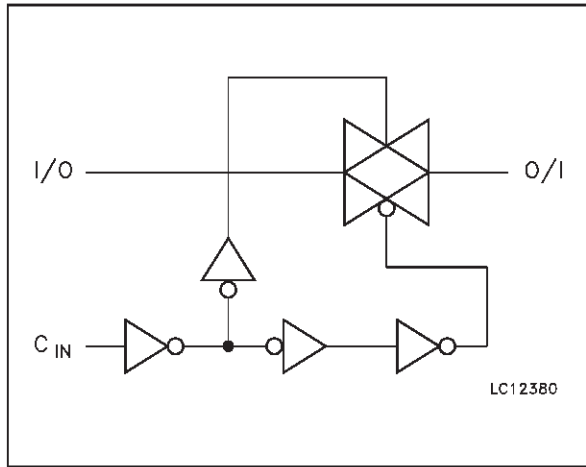
power-supply range (from  $V_{CC}$  to Ground).

The C input is provided to control the switch and it's compatible with standard CMOS output; the switch is ON when the C input is held high and off when C is held low. It can be used in many application as Battery Powered System, Audio Signal Routing, Communications System, Test Equipment. It's available in the commercial temperature range in SOT23-8L.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**LOGIC DIAGRAM**



**PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	1 to 2 I/O	Independent Input/Output
2, 6	1 to 2 O/I	Independent Output/Input
3, 7	1C to 2C	Enable Input (Active HIGH)
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>IC</sub>	DC Control Input Voltage	-0.5 to 7	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>IK</sub>	DC Control Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 100	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>IC</sub>	Control Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature:	-40 to +85	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 5.5V

2) V<sub>IN</sub> from 30% to 70%V<sub>CC</sub>

## DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
				T <sub>A</sub> = 25 °C			-40 to 85 °C		
				V <sub>CC</sub> (V)	Min.	Typ.	Max.	Min.	
V <sub>IH</sub>	High Level Control Input Voltage	2.0	1.5			1.5		V	
		2.7 to 5.5	0.7V <sub>CC</sub>			0.7V <sub>CC</sub>			
V <sub>IL</sub>	Low Level Control Input Voltage	2.0			0.5		0.5	V	
		2.7 to 5.5			0.3V <sub>CC</sub>		0.3V <sub>CC</sub>		
R <sub>ON</sub>	ON Resistance	3.3 <sup>(**)</sup>	V <sub>IC</sub> = V <sub>IH</sub> V <sub>I/O</sub> = V <sub>CC</sub> to GND I <sub>I/O</sub> ≤ 1mA		14	26		30	Ω
		5.0 <sup>(*)</sup>			12	17		20	
		3.3 <sup>(**)</sup>	V <sub>IC</sub> = V <sub>IH</sub> V <sub>I/O</sub> = V <sub>CC</sub> or GND I <sub>I/O</sub> ≤ 1mA		12	18		24	
		5.0 <sup>(*)</sup>			10	14		18	
ΔR <sub>ON</sub>	Difference of ON Resistance Between Switches	3.0 to 5.5	V <sub>IC</sub> = V <sub>IH</sub> V <sub>I/O</sub> = V <sub>CC</sub> to GND I <sub>I/O</sub> ≤ 1mA		2				Ω
I <sub>OFF</sub>	Input/Output Leakage Current (SWITCH OFF)	5.5	V <sub>OS</sub> = V <sub>CC</sub> to GND V <sub>IS</sub> = V <sub>CC</sub> to GND V <sub>IC</sub> = V <sub>IL</sub>			±0.1		±1.0	μA
I <sub>Iz</sub>	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	5.5	V <sub>OS</sub> = V <sub>CC</sub> to GND V <sub>IC</sub> = V <sub>IH</sub>			±0.1		±1.0	μA
I <sub>IN</sub>	Control Input Leakage Current	0 to 5.5	V <sub>IC</sub> = 5.5V or GND			±0.1		±1.0	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>IC</sub> = V <sub>CC</sub> or GND			1		10	μA

(\*) Voltage range is 5V ± 0.5V

(\*\*) Voltage range is 3.3V ± 0.3V

**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 3 \text{ ns}$ )

Symbol	Parameter	Test Condition		Value					Unit
				T <sub>A</sub> = 25 °C			-40 to 85 °C		
				V <sub>CC</sub> (V)	Min.	Typ.	Max.	Min.	
t <sub>PD</sub>	Delay Time	3.3 <sup>(*)</sup>	t <sub>r</sub> = t <sub>f</sub> = 6ns		0.4	0.8		1.2	ns
		5.0 <sup>(**)</sup>			0.3	0.6		1.0	
t <sub>PZL</sub> t <sub>PZH</sub>	Output Enable Time	3.3 <sup>(*)</sup>	R <sub>L</sub> = 1kΩ		2.5	4.0		5.0	ns
		5.0 <sup>(**)</sup>			2.0	4.0		5.0	
t <sub>PLZ</sub> t <sub>PHZ</sub>	Output Disable Time	3.3 <sup>(*)</sup>	R <sub>L</sub> = 500Ω		5.0	7.5		9.0	ns
		5.0 <sup>(**)</sup>			5.0	7.5		9.0	
C <sub>IN</sub>	Input Capacitance				5				pF
C <sub>I/O</sub>	Switch Terminal Capacitance				10				pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	3.3			2.5				pF
		5.0			3				

1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>IN</sub> + I<sub>CC</sub>/2 (switch).

(\*) Voltage range is 3.3V ± 0.3V

(\*\*) Voltage range is 5V ± 0.5V

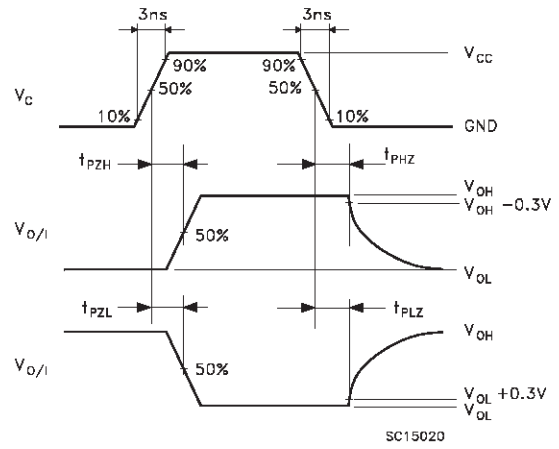
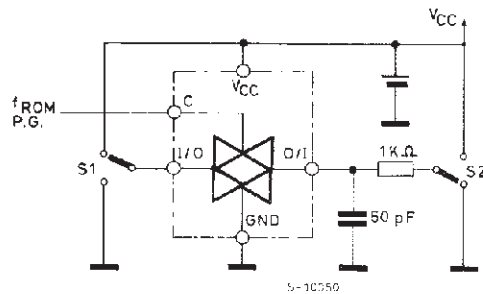
**ANALOG SWITCH CHARACTERISTICS** (GND = 0 V, T<sub>A</sub> = 25°C)

Symbol	Parameter	Test Condition			Value	Unit
		V <sub>CC</sub> (V)	V <sub>IN</sub> (Vp-p)			
	Sine Wave Distortion (THD)	3.3	2.75	f <sub>IN</sub> = 1 KHz R <sub>L</sub> = 10KΩ C <sub>L</sub> = 50 pF	0.04	%
		5.0 <sup>(*)</sup>	4		0.04	
f <sub>MAX</sub>	Frequency Response (Switch ON)	3.3	Adjust f <sub>IN</sub> voltage to Obtain 0dBm at V <sub>OS</sub> . Increase f <sub>IN</sub> Frequency until dB Meter reads -3dB R <sub>L</sub> = 50Ω, C <sub>L</sub> = 10pF		150	MHz
		5.0 <sup>(*)</sup>			180	
	Feedthrough Attenuation (Switch OFF)	3.3	V <sub>IN</sub> is centered at V <sub>CC</sub> /2. Adjust f <sub>IN</sub> voltage to obtain 0dBm at V <sub>IS</sub> R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF, f <sub>IN</sub> = 1MHz sine wave		-60	dB
		5.0 <sup>(*)</sup>			-60	
	Crosstalk (Control Input to Signal Output)	3.3	R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF, f <sub>IN</sub> = 1MHz square wave t <sub>r</sub> = t <sub>f</sub> = 6ns		60	mV
		5.0 <sup>(*)</sup>			60	
	Crosstalk (Between Switches)	3.3	R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF, f <sub>IN</sub> = 1MHz sine wave		-60	dB
		5.0 <sup>(*)</sup>			-60	

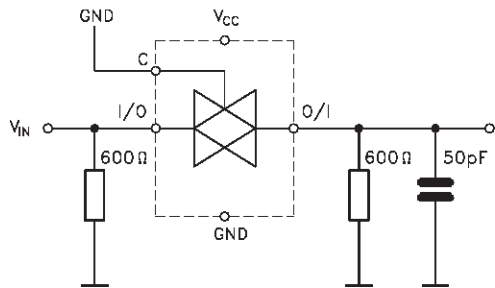
(\*) Voltage range is 5V ± 0.5V

SWITCHING CHARACTERISTICS TEST CIRCUIT

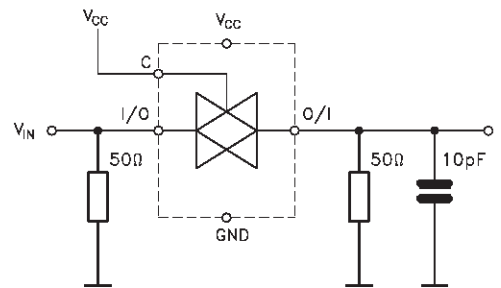
$t_{PLZ}$ ,  $t_{PHZ}$ ,  $t_{PZL}$ ,  $t_{PZH}$ .



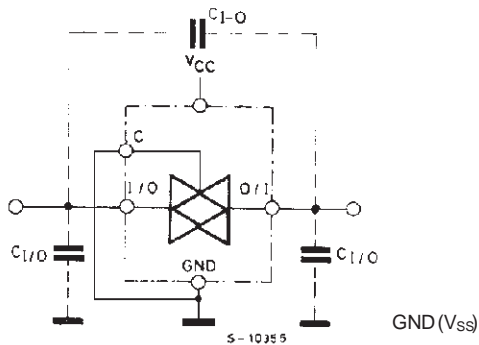
FEEDTHROUGH ATTENUATION



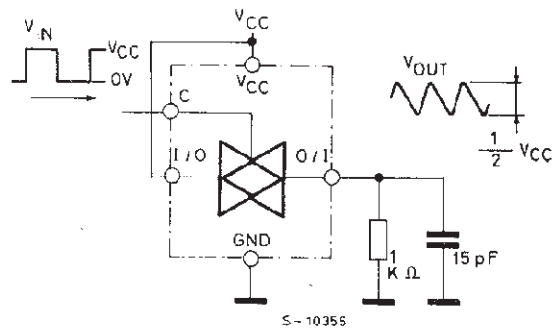
BANDWIDTH ATTENUATION



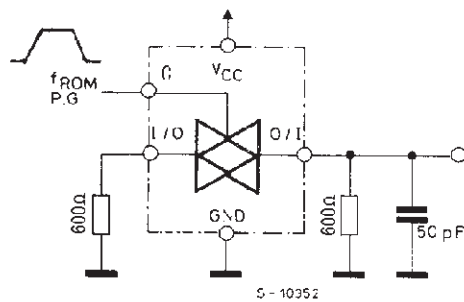
$C_{I-O}$   $C_{I/O}$



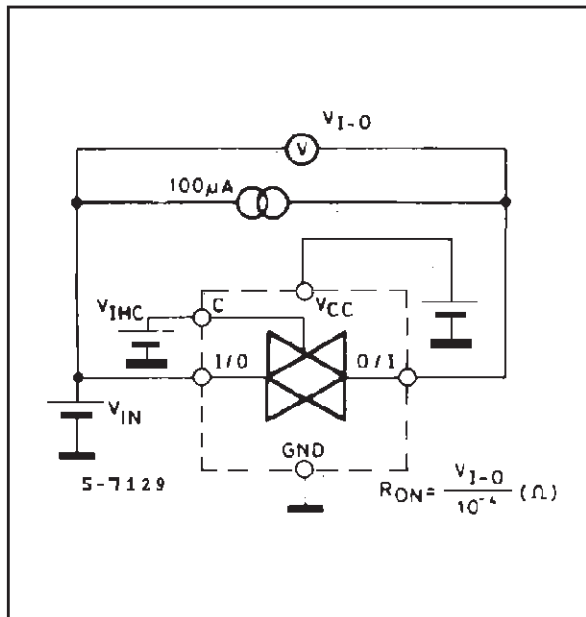
MAXIMUM CONTROL FREQUENCY



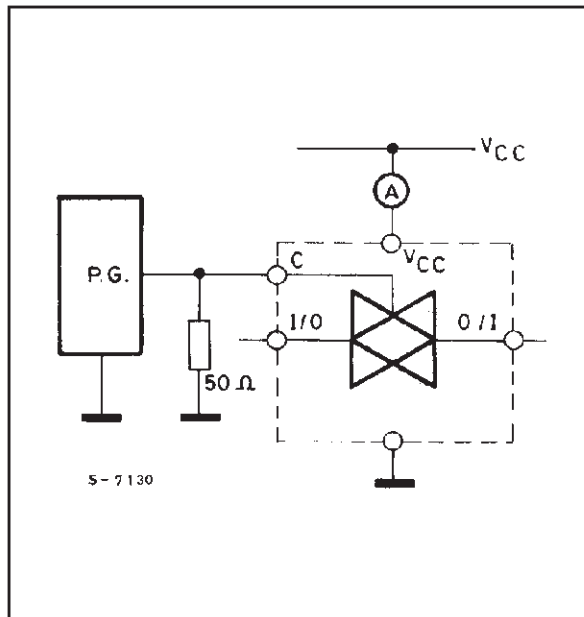
CROSSTALK (control to output)



CHANNEL RESITANCE (RON)

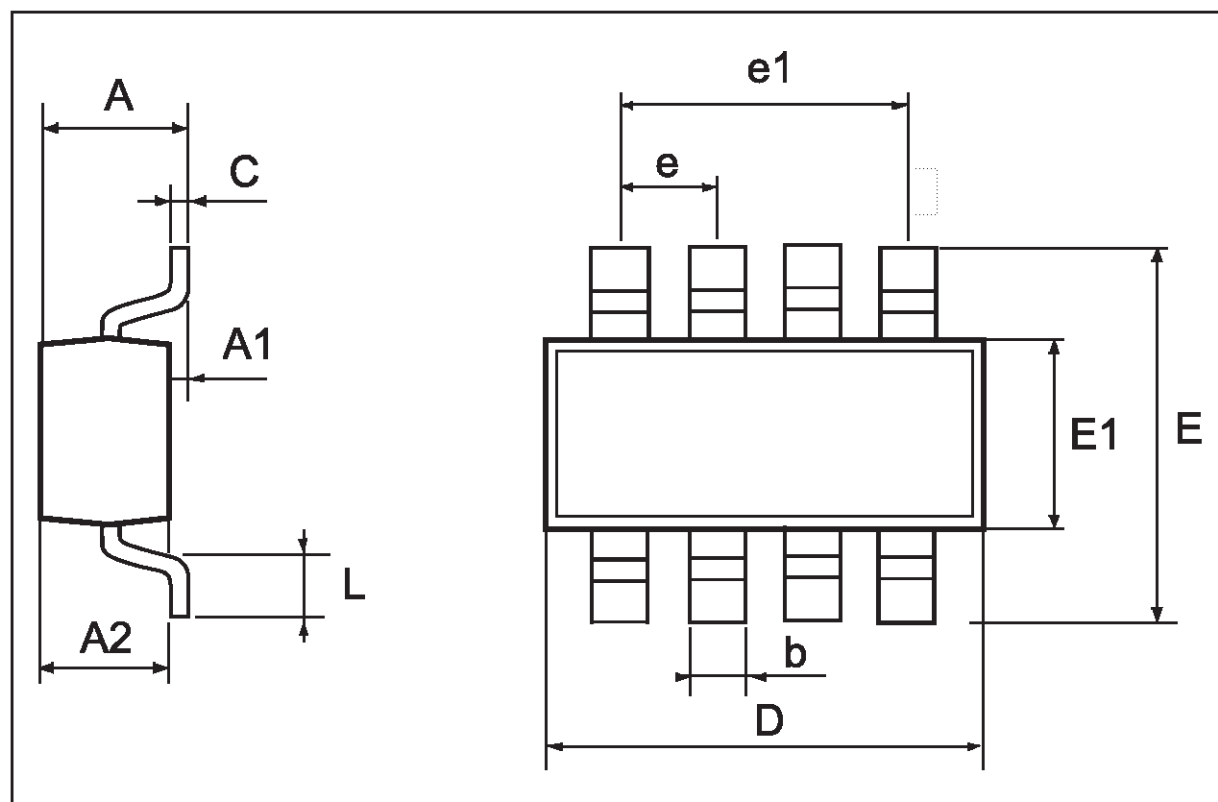


I<sub>cc</sub> (Opr.)



## SOT23-8L MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
L	0.35		0.55	13.8		21.6
e		0.65			25.6	
e1		1.95			76.7	



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